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Vishay Semiconductors

High Speed Infrared Emitting Diodes, 850 nm, Surface Emitter Technology



DESCRIPTION

As part of the <u>SurfLight</u> portfolio, the VSMY1850 is an infrared, 850 nm emitting diode based on GaAlAs surface emitter chip technology with high radiant intensity, high optical power and high speed, molded in clear, untinted 0805 plastic package for surface mounting (SMD).

FEATURES

- Package type: surface mount
- Package form: 0805
- Dimensions (L x W x H in mm): 2 x 1.25 x 0.85
- Peak wavelength: λ_p = 850 nm
- High reliability
- · High radiant power
- High radiant intensity
- High speed
- Angle of half sensitivity: $\varphi = \pm 60^{\circ}$
- · Suitable for high pulse current operation
- 0805 standard surface-mountable package
- Floor life: 168 h, MSL 3, according to J-STD-020
- · Lead (Pb)-free reflow soldering
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- IrDA compatible data transmission
- · Miniature light barrier
- Photointerrupters
- · Optical switch
- Emitter source for proximity sensors
- IR touch panels
- IR Flash
- IR illumination
- 3D TV

PRODUCT SUMMARY					
COMPONENT	I _e (mW/sr)	φ (deg)	λ _p (nm)	t _r (ns)	
VSMY1850	10	± 60	850	10	

Note

• Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
VSMY1850	Tape and reel	MOQ: 3000 pcs, 3000 pcs/reel	0805	

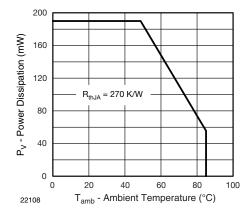
Note

MOQ: minimum order quantity



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ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	5	V	
Forward current		I _F	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I _{FM}	200	mA	
Surge forward current	t _p = 100 μs	I _{FSM}	1	А	
Power dissipation		P _V	190	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	-40 to +85	°C	
Storage temperature range		T _{stg}	-40 to +100	°C	
Soldering temperature	According to Fig. 7, J-STD-020	T _{sd}	260	°C	
Thermal resistance junction / ambient	JESD 51	R _{thJA}	270	K/W	





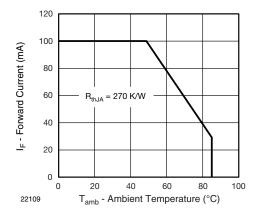


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward valtage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V _F	-	1.65	1.9	V
Forward voltage	$I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$	V _F	-	2.9	-	V
Tamananatura anaffiniant of V	I _F = 1 mA	TK _{VF}	-	-1.4	-	mV/K
Temperature coefficient of V _F	I _F = 10 mA	TK _{VF}	-	-1.18	=	mV/K
Reverse current		I _R	Not designed for reverse operation		μA	
Junction capacitance	$V_R = 0 \text{ V, f} = 1 \text{ MHz,}$ $E = 0 \text{ mW/cm}^2$	CJ	-	125	-	pF
Redient intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l _e	5	10	15	mW/sr
Radiant intensity	$I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$	l _e	-	85	-	mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фе	-	50	-	mW
Temperature coefficient of radiant power	I _F = 100 mA	TKφ _e	-	-0.35	-	%/K
Angle of half intensity		φ	-	± 60	=	deg
Peak wavelength	I _F = 100 mA	λρ	840	850	870	nm
Spectral bandwidth	I _F = 30 mA	Δλ	-	30	=	nm
Temperature coefficient of λ _p	I _F = 30 mA	TK _{λp}	-	0.25	=	nm/K
Rise time	I _F = 100 mA, 20 % to 80 %	t _r	-	10	-	ns
Fall time	I _F = 100 mA, 20 % to 80 %	t _f	-	10	-	ns
Virtual source diameter		d	-	0.5	-	mm



BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

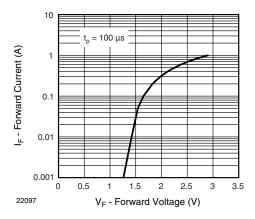


Fig. 3 - Forward Current vs. Forward Voltage

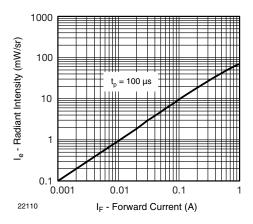


Fig. 4 - Radiant Intensity vs. Forward Current

REFLOW SOLDER PROFILE

19841

300 250 245 °C 240 °C 217 °C Temperature (°C) 200 max. 30 s 150 max. 120 s max. 100 s 100 max. ramp down 6 °C/s 50 nax. ramp up 3 °C/s 50 100 300 150 200

Fig. 7 - Lead (Pb)-free Reflow Solder Profile According to J-STD-020

Time (s)

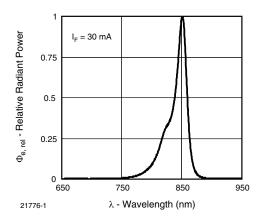


Fig. 5 - Relative Radiant Power vs. Wavelength

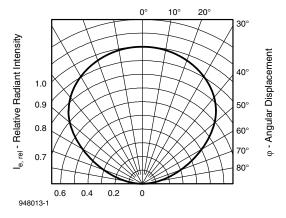


Fig. 6 - Relative Radiant Intensity vs. Angular Displacement

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 3

Floor life: 168 h

Conditions: T_{amb} < 30 °C, RH < 60 %

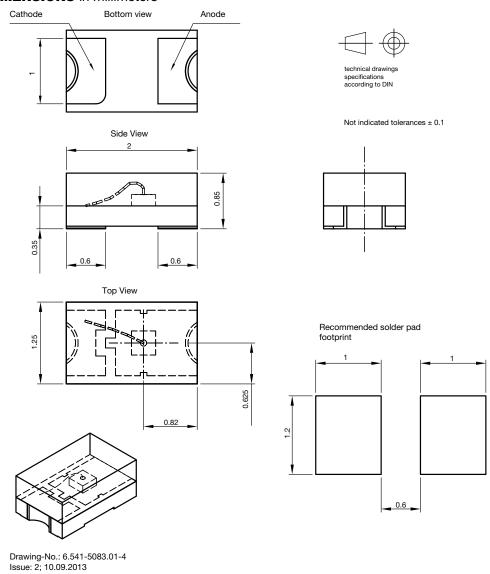
DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 $^{\circ}$ C (+ 5 $^{\circ}$ C), RH < 5 $^{\circ}$ M.



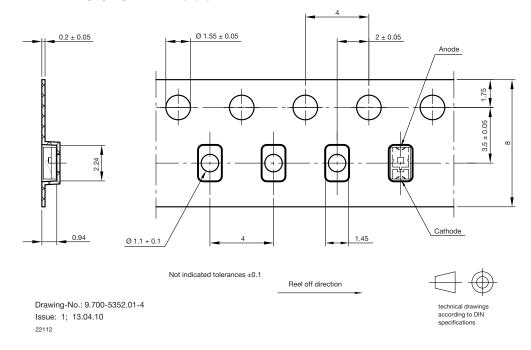
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PACKAGE DIMENSIONS in millimeters



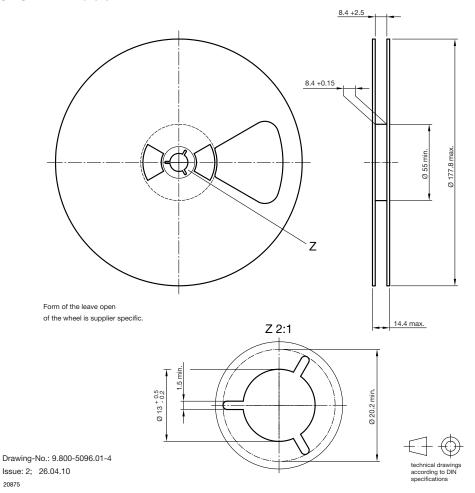


BLISTER TAPE DIMENSIONS in millimeters



REEL DIMENSIONS in millimeters

20875





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